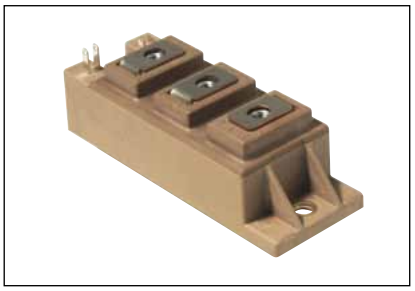
1MBI100U4F-120L-50

IGBT Modules

IGBT MODULE (U series)
1200V / 100A / 1 in one package

Features

High speed switching
Voltage drive
Low Inductance module structure



Applications

Inverter DB for Motor Drive
AC and DC Servo Drive Amplifier (DB)
Active PFC
Industrial machines

Maximum Ratings and Characteristics

● **Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)**

Items		Symbols	Conditions		Maximum ratings	Units
Collector-Emitter voltage		V_{CES}			1200	V
Gate-Emitter voltage		V_{GES}			±20	V
Collector current		Ic	Continuous	Tc=25°C	150	A
				Tc=80°C	100	
		Ic pulse	1ms	Tc=25°C	300	
				Tc=80°C	200	
		-Ic			50	
		-Ic pulse	1ms		100	
Collector power dissipation		Pc	1 device		540	W
Reverse voltage for FWD		VR			1200	V
Forword current for FWD		IF	Continuous		150	A
		IF pulse	1ms		300	
Junction temperature		Tj			+150	°C
Storage temperature		Tstg			-40~+125	°C
Isolation voltage	Between terminal and copper base (*1)	V_{iso}	AC : 1min.		2500	VAC
Screw torque	Mounting (*2)	-			3.5	Nm
	Terminals (*3)					

Note *1: All terminals should be connected together when isolation test will be done.
Note *2: Recommendable Value : 2.5 to 3.5 Nm (M5 or M6)
Note *3: Recommendable Value : 2.5 to 3.5 Nm (M5)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items	Symbols	Conditions		Characteristics min.	Characteristics typ.	Characteristics max.	Units
Zero gate voltage collector current	I_{CES}	V_{GE} = 0V, V_{CE} = 1200V		-	-	1.0	mA
Gate-Emitter leakage current	I_{GES}	V_{CE} = 0V, V_{GE} = ±20V		-	-	200	nA
Gate-Emitter threshold voltage	$V_{GE\ (th)}$	V_{CE} = 20V, I_C = 100mA		4.5	6.5	8.5	V
Collector-Emitter saturation voltage	$V_{CE\ (sat)}$ (terminal)	V_{GE} = 15V, I_C = 100A	Tj=25°C	-	2.05	2.20	V
			Tj=125°C	-	2.25	-	
	$V_{CE\ (sat)}$ (chip)		Tj=25°C	-	1.90	2.05	
			Tj=125°C	-	2.10	-	
Input capacitance	Cies	V_{GE} = 0V, V_{CE} = 10V, f = 1MHz		-	11	-	nF
Turn-on time	ton	V_{CC} = 600V, I_C = 100A, V_{GE} = ±15V, R_G = 5.6Ω		-	0.32	1.20	μs
	tr			-	0.10	0.60	
	tr(i)			-	0.03	-	
Turn-off time	toff			-	0.41	1.00	
	tf			-	0.07	0.30	
Forward on voltage	V_F (terminal)	V_{GE} = 0V, I_F = 50A	Tj=25°C	-	1.70	2.00	V
			Tj=125°C	-	1.80	-	
	V_F (chip)		Tj=25°C	-	1.60	1.85	
			Tj=125°C	-	1.70	-	
Reverse Current	IR	V_{CE} = 1200V		-	-	1.0	mA
Forward on voltage	V_F (terminal)	V_{GE} = 0V, I_F = 150A	Tj=25°C	-	1.85	2.00	V
			Tj=125°C	-	2.00	-	
	V_F (chip)		Tj=25°C	-	1.60	1.75	
			Tj=125°C	-	1.75	-	
Reverse recovery time	trr	I_F = 150A		-	-	0.35	μs
Lead resistance, terminal-chip(*4)	R lead			-	1.39	-	mΩ

Note *4: Biggest internal terminal resistance among arm.

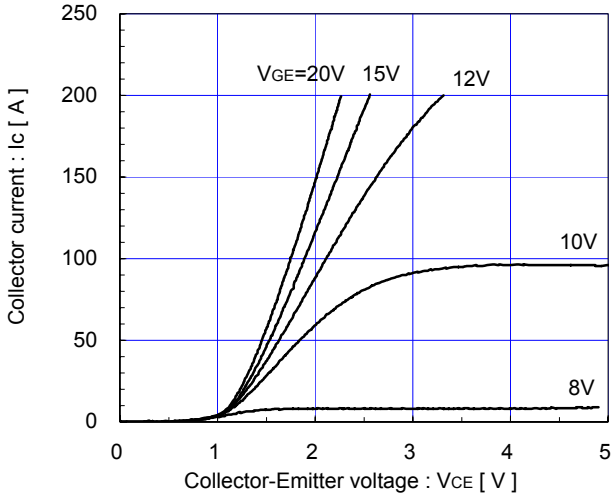
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics min.	Characteristics typ.	Characteristics max.	Units
Thermal resistance (1device)	Rth(j-c)	IGBT	-	-	0.23	°C/W
		Inverse Diode	-	-	0.73	
		FWD	-	-	0.28	
Contact thermal resistance	Rth(c-f)	with Thermal Compound (*5)	-	0.05	-	

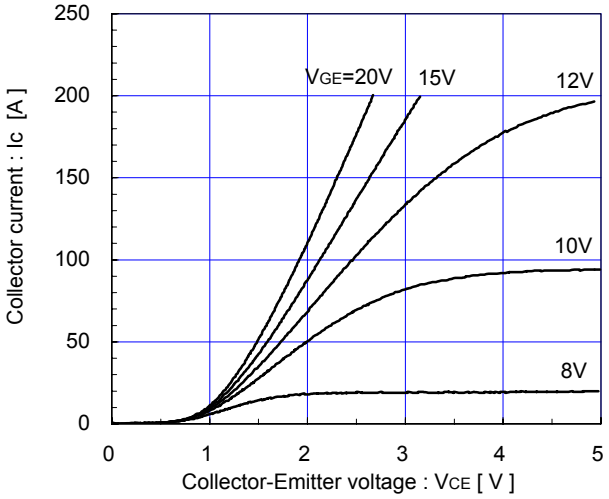
Note *5: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

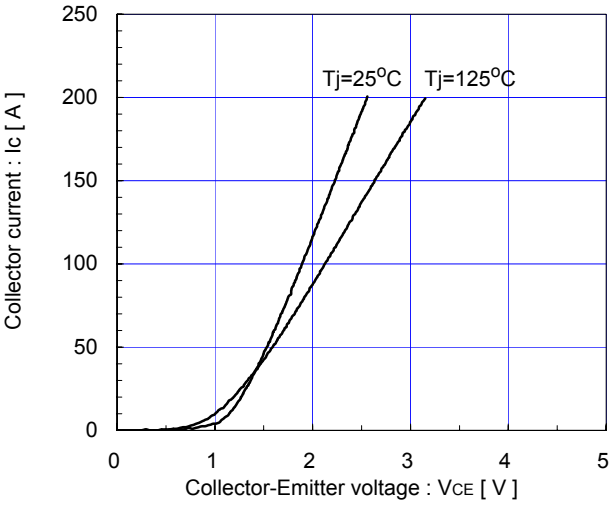
Collector current vs. Collector-Emitter voltage (typ.)
Tj=25°C / chip



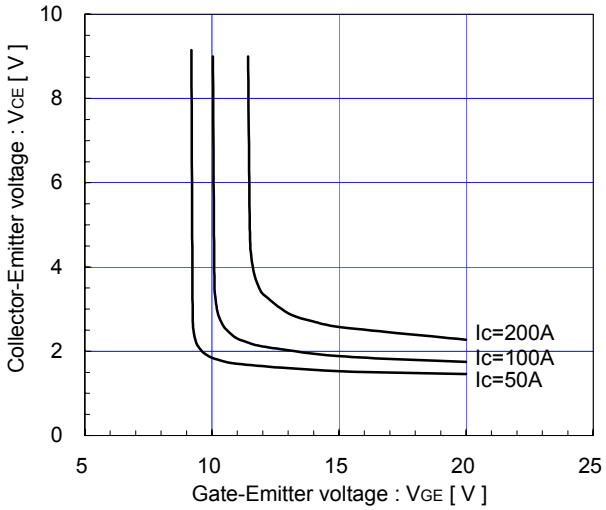
Collector current vs. Collector-Emitter voltage (typ.)
Tj=125°C / chip



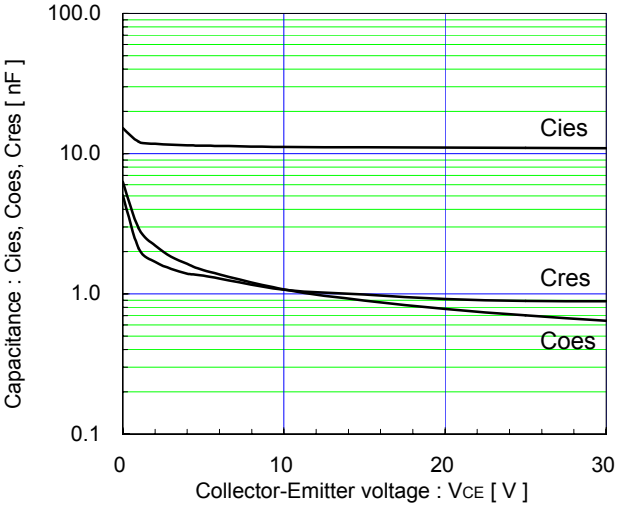
Collector current vs. Collector-Emitter voltage (typ.)
VGE=15V / chip



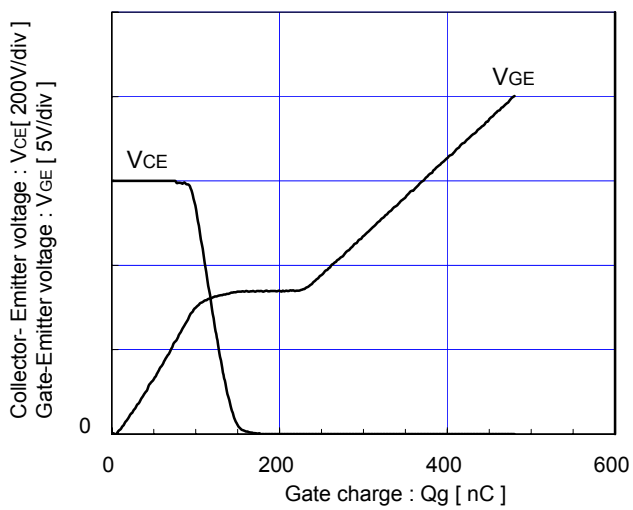
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)
Tj=25°C / chip



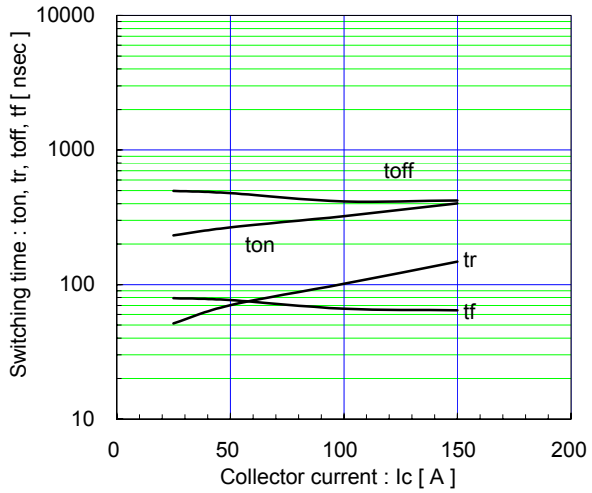
Capacitance vs. Collector-Emitter voltage (typ.)
VGE=0V, f=1MHz, Tj=25°C



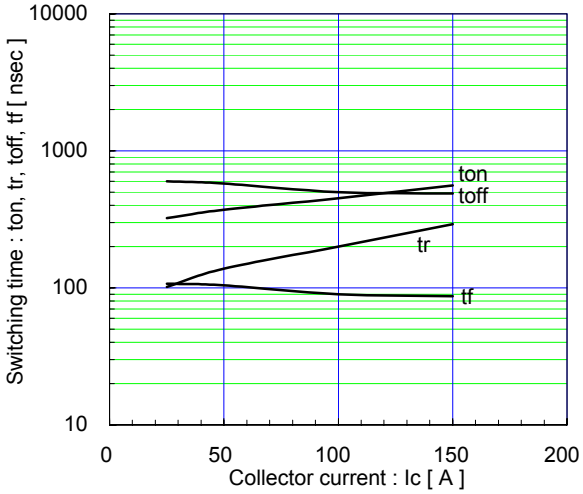
Dynamic Gate charge (typ.)
Vcc=600V, Ic=100A, Tj=25°C



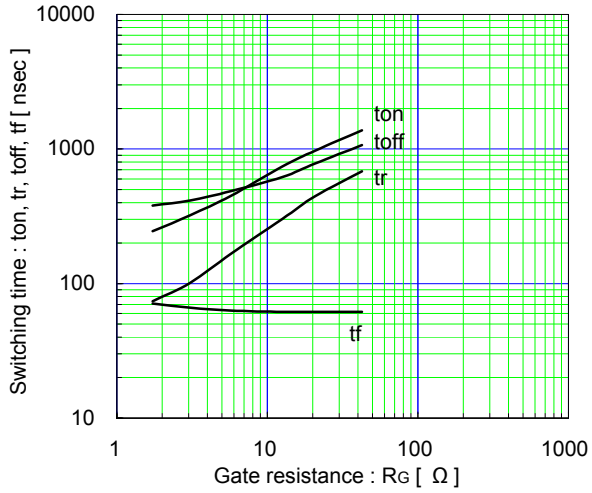
Switching time vs. Collector current (typ.)
Vcc=600V, VGE=±15V, RG=5.6Ω, Tj=25°C



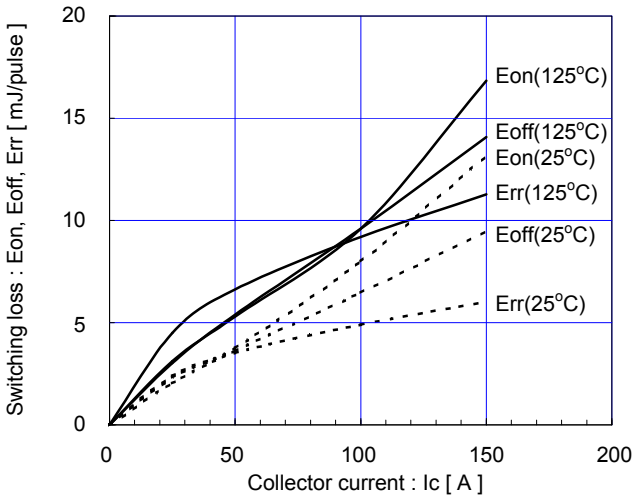
Switching time vs. Collector current (typ.)
Vcc=600V, VGE=±15V, RG=5.6Ω, Tj=125°C



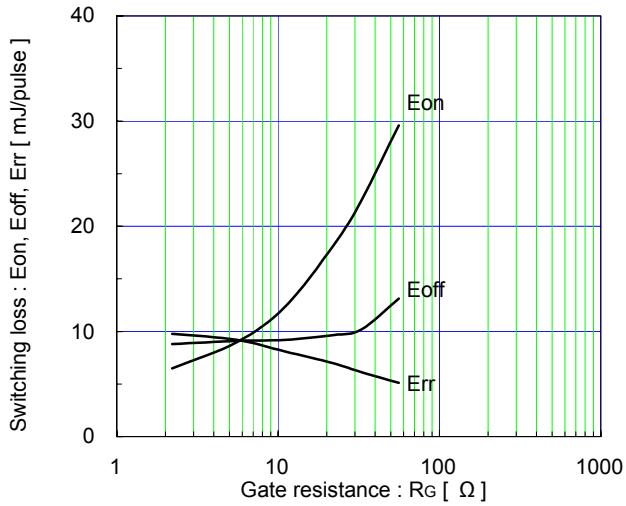
Switching time vs. Gate resistance (typ.)
Vcc=600V, Ic=100A, VGE=±15V, Tj=25°C



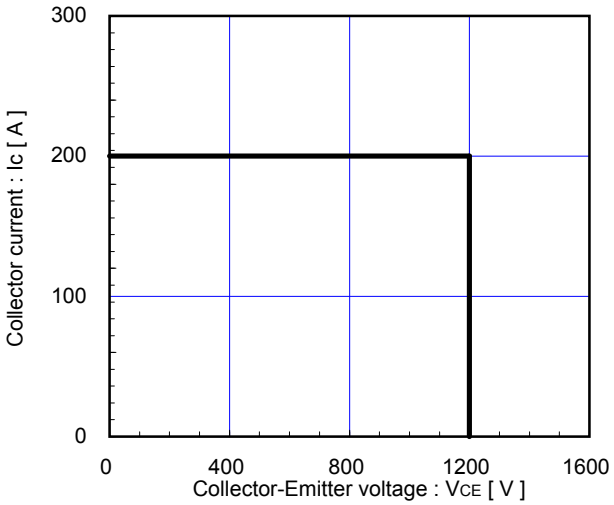
Switching loss vs. Collector current (typ.)
Vcc=600V, VGE=±15V, RG=5.6Ω



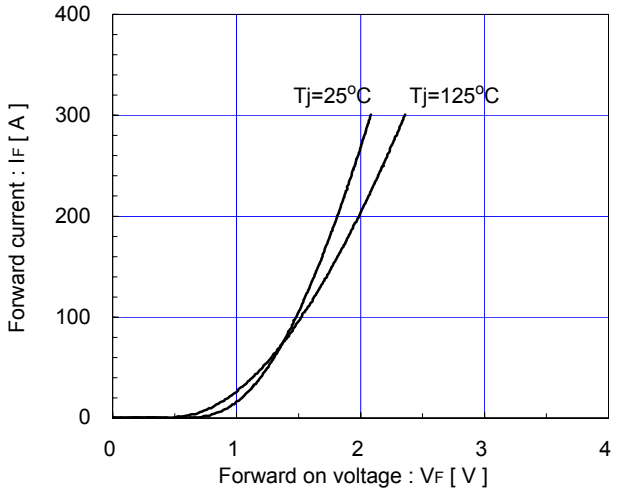
Switching loss vs. Gate resistance (typ.)
Vcc=600V, Ic=100A, VGE=±15V, Tj=125°C



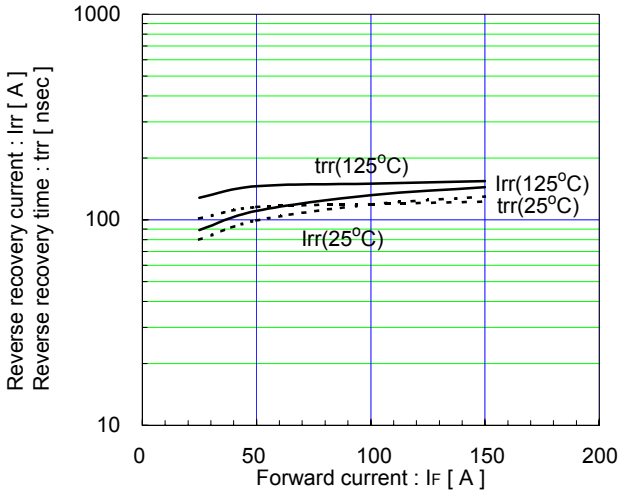
Reverse bias safe operating area (max.)
+VGE=15V, -VGE <= 15V, RG >= 5.6Ω,Tj <= 125°C



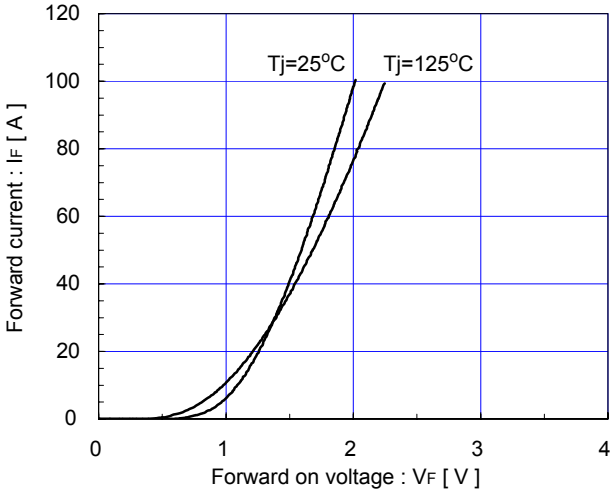
FWD
Forward current vs. Forward on voltage (typ.)
chip



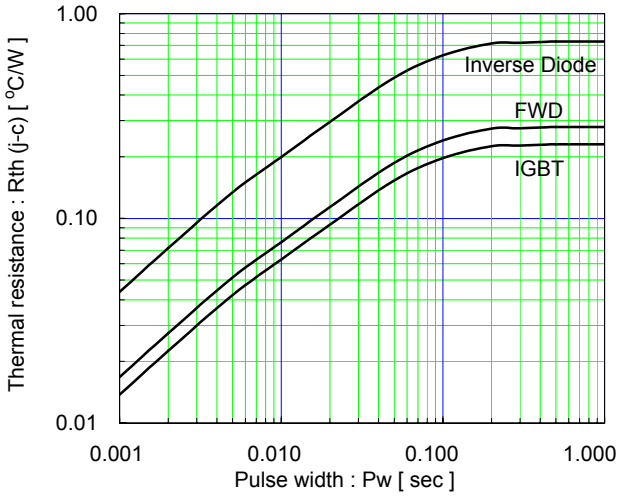
FWD
Reverse recovery characteristics (typ.)
Vcc=600V, VGE=±15V, RG=5.6Ω



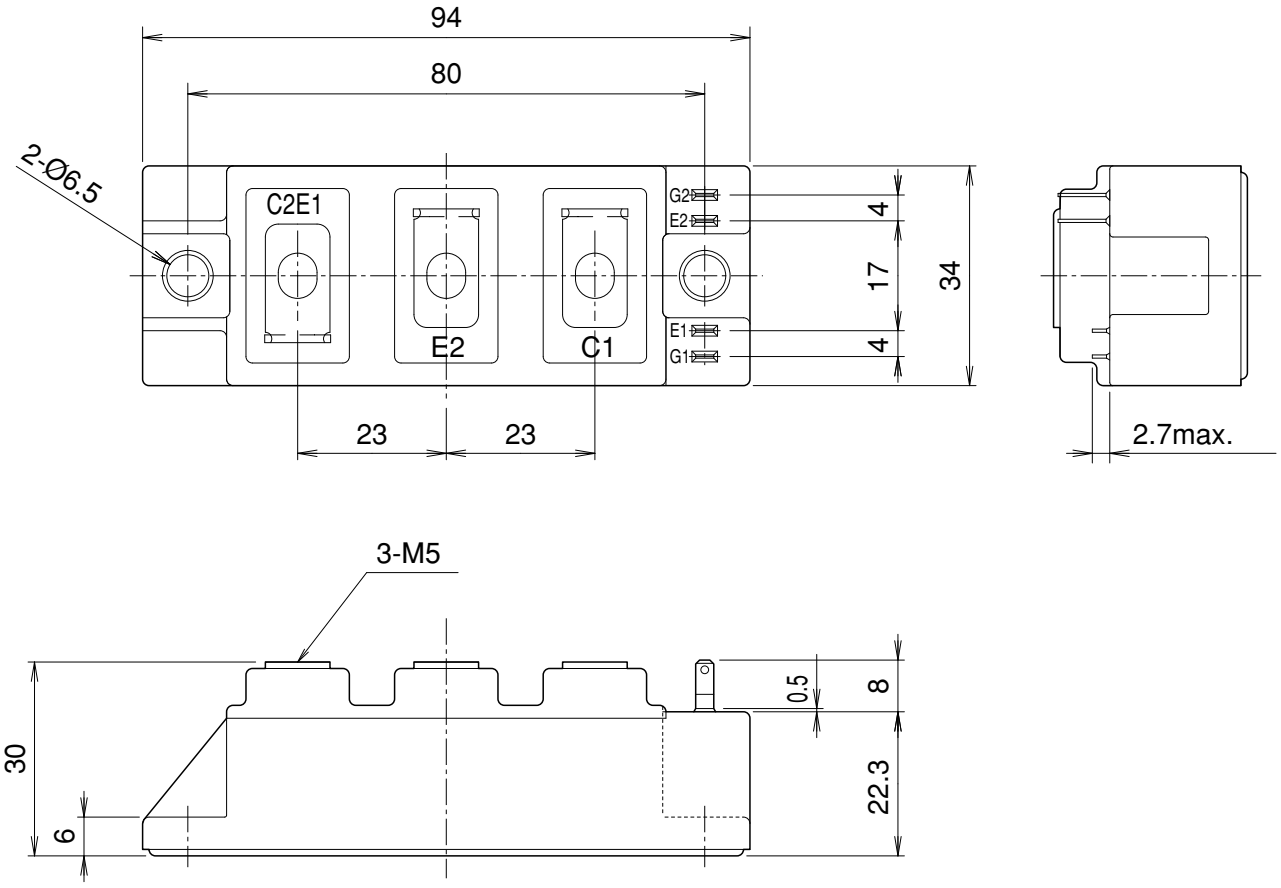
Inverse Diode
Forward current vs. Forward on voltage (typ.)
chip



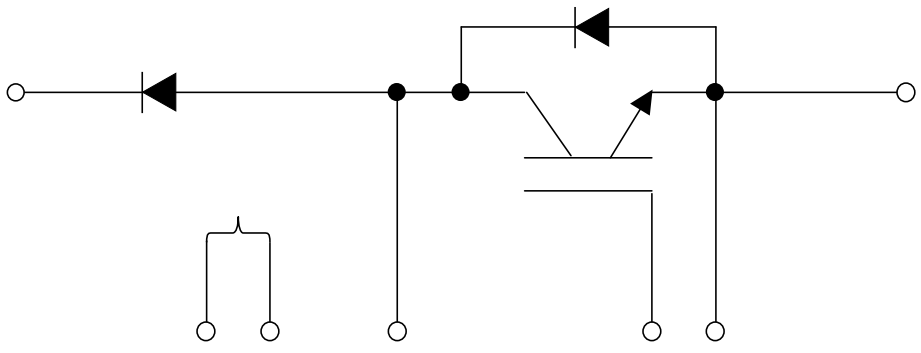
Transient thermal resistance (max.)



■ Outline Drawings, mm



■ Equivalent Circuit Schematic



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- Machine tools
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- Personal equipment
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- Emergency equipment for responding to disasters and anti-burglary devices
- Safety devices
- Medical equipment

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富士電機

Innovating Energy Technology

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IGBT Modules

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